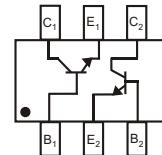




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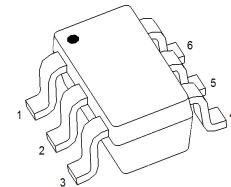
8AAH ) ) %G

TRANSISTOR (NPN+NPN)



## FEATURES

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching



SOT-23 -6L

MARKING: 5551S

## MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_c$	Collector Current	600	mA
$P_c$	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	°C/W
$T_j, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	°C

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

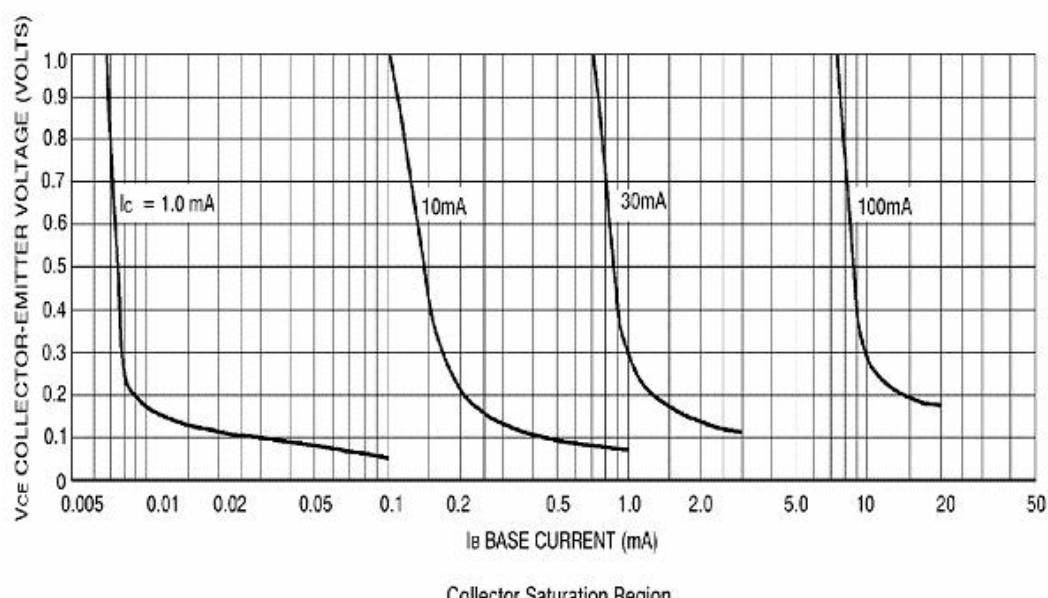
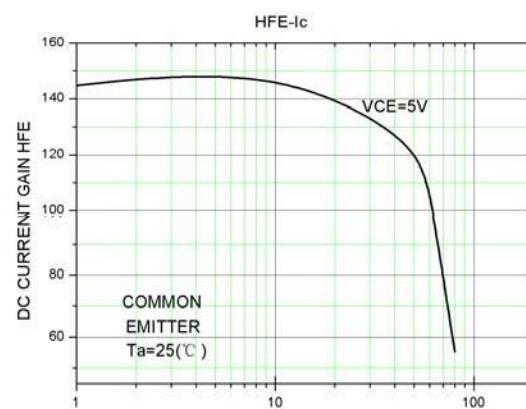
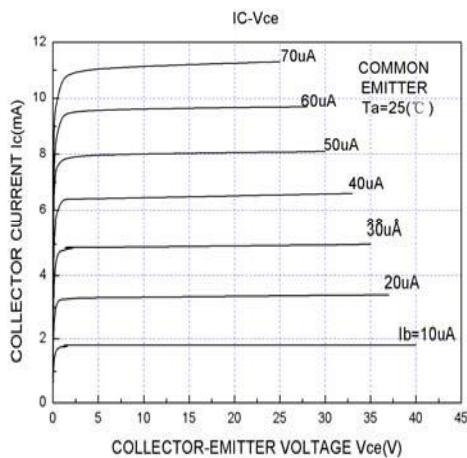
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=1\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=120\text{V}, I_E=0$			50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			50	nA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	80			
	$h_{FE(2)}^*$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	100		300	
	$h_{FE(3)}^*$	$V_{CE}=5\text{V}, I_C=50\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.15	V
	$V_{CE(sat)2}^*$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)1}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			1	V
	$V_{BE(sat)2}^*$	$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100		300	MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			6	pF

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .



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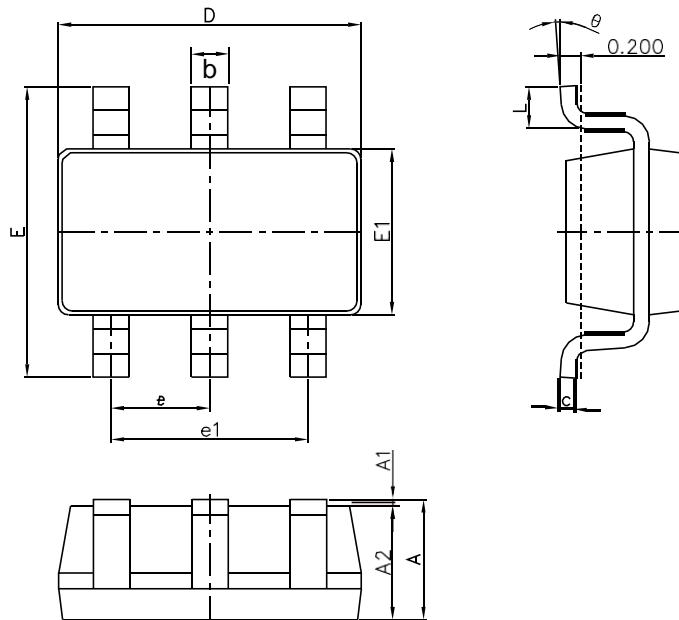
## Typical Characteristics





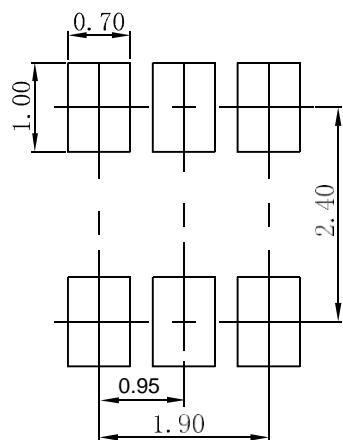
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### SOT-23-6L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

### SOT-23-6L Suggested Pad Layout



#### Note:

1. Controlling dimension:in millimeters.
- 2.General tolerance: $\pm 0.05\text{mm}$ .
- 3.The pad layout is for reference purposes only.